

SLCD-61N1

Solderable Planar Photodiode

Features

- Visible to IR spectral irradiance range
- High reliability
- Oxide passivation
- Linear short circuit current
- Low capacitance, high speed
- Available in arrays where # indicates number of elements (maximum of 9 elements)

Description

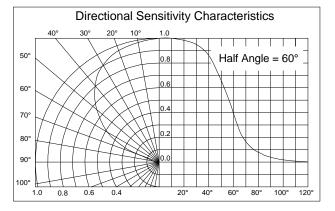
The Silonex series of silicon solderable planar photodiodes feature low cost, high reliability, and linear short circuit current over a wide range of illumination. These devices are widely used for light sensing and power generation because of their stability and high efficiency. They are particularly suited to power conversion applications due to their low internal impedance, relatively high shunt impedance, and stability. These devices also provide a reliable, inexpensive detector for applications such as light beam sensing and instrumentation. The electrical characteristics below are per element. In the multi-element arrays the cathodes are common to all elements.

Absolute Maximum Ratings

Storage Temperature	-40°C to +125°C
Operating Temperature	-40°C to +125°C

Cathode Cathode Sensitive Area (10.4 sq. mm.) Dimensions in mm. (+/- 0.13)

Also available with leads as part number SLSD-71N1



Electrical Characteristics (T_A=25°C unless otherwise noted) Symbol Parameter Min Мах Units **Test Conditions** Тур Short Circuit Current 0.4 $V_{R}=0V, Ee=25mW/cm^{2}$ (1) 0.5 mΑ I_{SC} $Ee=25mw/cm^2$ (1) Voc Open Circuit Voltage 0.40 V Reverse Dark Current μΑ $V_R=5V, Ee=0$ 1.7 I_{D} CJ Junction Capacitance 0.4 nF $V_{R}=0V$, Ee=0, f=1MHz Spectral Sensitivity 0.55 A/W S_{λ} λ=940nm Reverse Breakdown Voltage V_{BR} 20 V I_R=100μA Maximum Sensitivity Wavelength 930 λ_{P} nm Sensitivity Spectral Range 400 1100 nm λ_R Acceptance Half Angle 60 deg $\theta_{1/2}$

Specifications subject to change without notice

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Notes: (1) Ee = light source @ 2854 °K